

Abstract of the Disclosure:

A process for the deposition of thin layers by chemical vapor deposition includes adding an effective amount of nitroxyl radicals of the formula



to a gas stream including the materials to be deposited. In this formula, R_1 and R_2 are identical or different alkyl, alkenyl, alkynyl, acyl, or aryl radicals, with or without heteroatoms. R_1 and R_2 can also together form a structure - $CR_3R_4-CR_5R_6-CR_7R_8-CR_9R_{10}-CR_{11}R_{12}-$, where $R_3, R_4, R_5, R_6, R_7, R_8, R_9, R_{10}, R_{11}, R_{12}$ are again identical or different alkyl, alkenyl, alkynyl, acyl, or aryl radicals, with or without heteroatoms.

LDP/vs